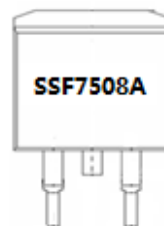
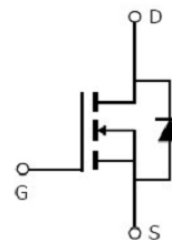


Main Product Characteristics:

V_{DSS}	75V
$R_{DS(on)}$	6m Ω (typ.)
I_D	100A


D2PAK

**Marking and pin
Assignment**

Schematic diagram
Features and Benefits:

- Advanced MOSFET process technology
- Special designed for PWM, load switching and general purpose applications
- Ultra low on-resistance with low gate charge
- Fast switching and reverse body recovery
- 175°C operating temperature


Description:

It utilizes the latest processing techniques to achieve the high cell density and reduces the on-resistance with high repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in power switching application and a wide variety of other applications.

Absolute max Rating:

Symbol	Parameter	Max.	Units
$I_D @ TC = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ ①	100	A
$I_D @ TC = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ ①	70	
I_{DM}	Pulsed Drain Current ②	400	
$P_D @ TC = 25^\circ C$	Power Dissipation ③	200	W
	Linear Derating Factor	1.3	W/°C
V_{DS}	Drain-Source Voltage	75	V
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy @ $L=0.3mH$ ②	205	mJ
I_{AS}	Avalanche Current @ $L=0.3mH$ ②	37	A
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C

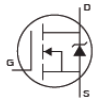
Thermal Resistance

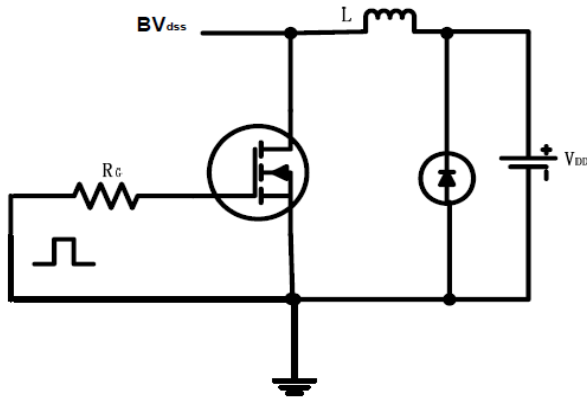
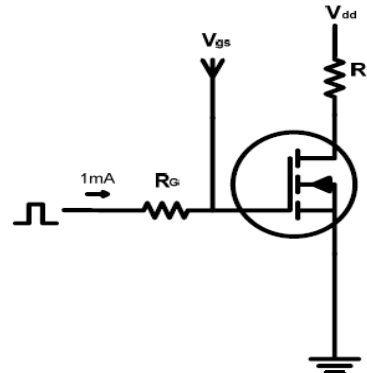
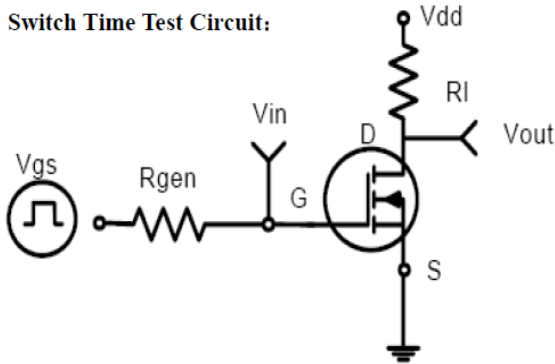
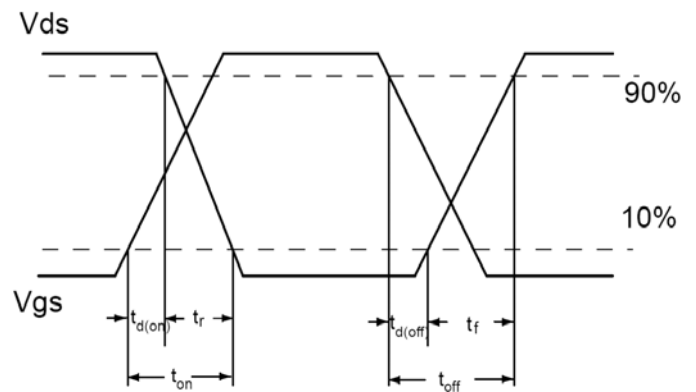
Symbol	Characterizes	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-case ^③	—	0.75	°C/W
$R_{\theta JA}$	Junction-to-ambient (t ≤ 10s) ^④	—	62	°C/W
	Junction-to-Ambient (PCB mounted, steady-state) ^④	—	40	°C/W

Electrical Characterizes @ $T_A=25^\circ\text{C}$ unless otherwise specified

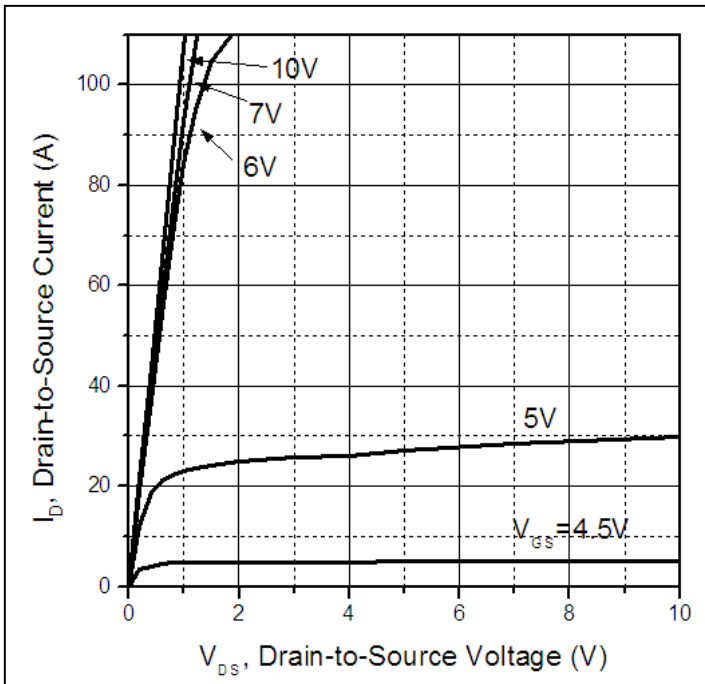
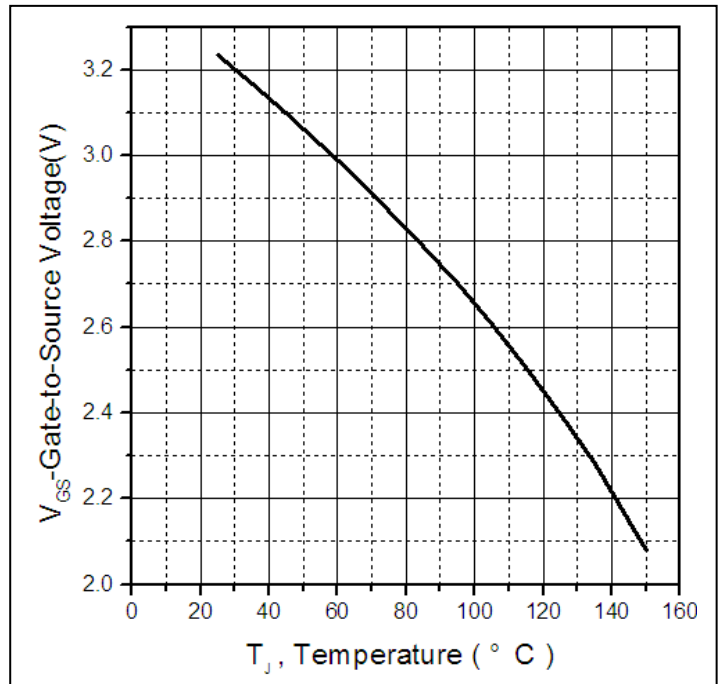
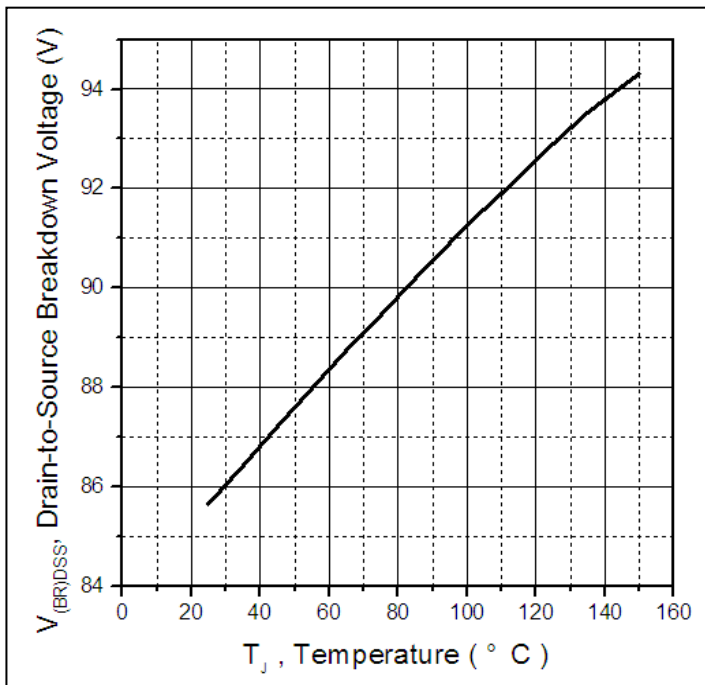
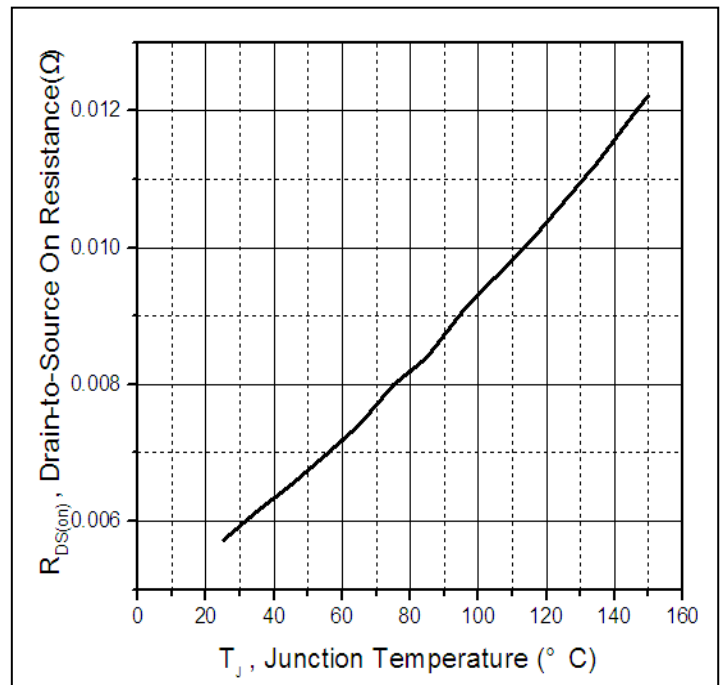
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source breakdown voltage	75	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$R_{DS(on)}$	Static Drain-to-Source on-resistance	—	6	8	mΩ	$V_{GS}=10V, I_D = 30A$ $T_J = 125^\circ\text{C}$
		—	10.5	—		
$V_{GS(th)}$	Gate threshold voltage	2	—	4	V	$V_{DS} = V_{GS}, I_D = 250\mu A$ $T_J = 125^\circ\text{C}$
		—	2.4	—		
I_{DSS}	Drain-to-Source leakage current	—	—	1	μA	$V_{DS} = 75V, V_{GS} = 0V$ $T_J = 125^\circ\text{C}$
		—	—	50		
I_{GSS}	Gate-to-Source forward leakage	—	—	100	nA	$V_{GS} = 20V$ $V_{GS} = -20V$
		—	—	-100		
Q_g	Total gate charge	—	118	—	nC	$I_D = 30A,$ $V_{DS}=30V,$ $V_{GS} = 10V$
Q_{gs}	Gate-to-Source charge	—	25	—		
Q_{gd}	Gate-to-Drain("Miller") charge	—	43	—		
$t_{d(on)}$	Turn-on delay time	—	20	—	ns	$V_{GS}=10V, V_{DS}=30V,$ $R_L=15\Omega,$ $R_{GEN}=2.55\Omega$
t_r	Rise time	—	18	—		
$t_{d(off)}$	Turn-Off delay time	—	67	—		
t_f	Fall time	—	26	—		
C_{iss}	Input capacitance	—	4972	—	pF	$V_{GS} = 0V,$ $V_{DS} = 25V,$ $f = 800\text{KHz}$
C_{oss}	Output capacitance	—	402	—		
C_{rss}	Reverse transfer capacitance	—	366	—		

Source-Drain Ratings and Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	100	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode)	—	—	400	A	
V_{SD}	Diode Forward Voltage	—	0.88	1.3	V	$I_S=30A, V_{GS}=0V$
t_{rr}	Reverse Recovery Time	—	45.7	—	ns	$T_J = 25^\circ\text{C}, I_F = 75A,$
Q_{rr}	Reverse Recovery Charge	—	91	—	nC	$di/dt = 100A/\mu s$

Test circuits and Waveforms
EAS test circuits:

Gate charge test circuit:

Switch Time Test Circuit:

Switch Waveforms:

Notes:

- ① Calculated continuous current based on maximum allowable junction temperature.
- ② Repetitive rating; pulse width limited by max. junction temperature.
- ③ The power dissipation PD is based on max. junction temperature, using junction-to-case thermal resistance.
- ④ The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$

Typical electrical and thermal characteristics

Figure 1: Typical Output Characteristics

Figure 2. Gate to source cut-off voltage

Figure 3. Drain-to-Source Breakdown Voltage vs. Temperature

Figure 4: Normalized On-Resistance Vs. Case Temperature

Typical electrical and thermal characteristics

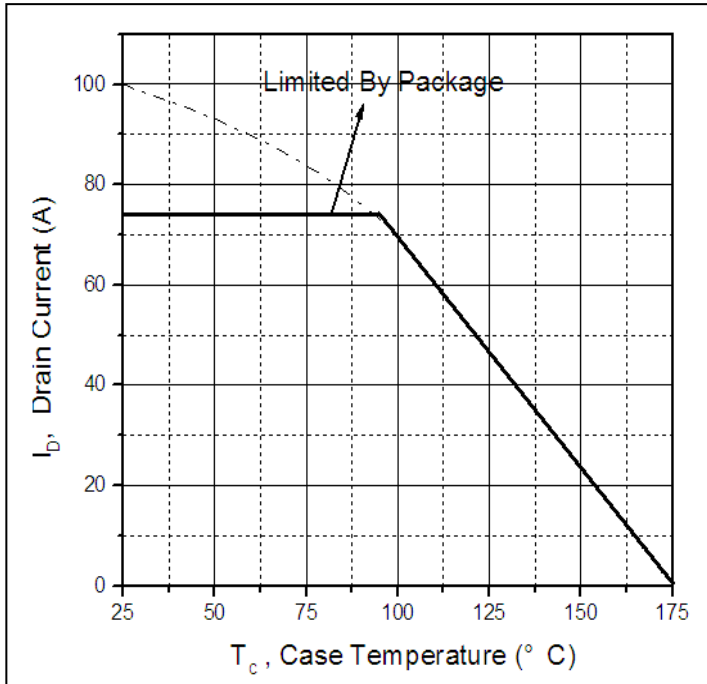


Figure 5. Maximum Drain Current Vs. Case Temperature

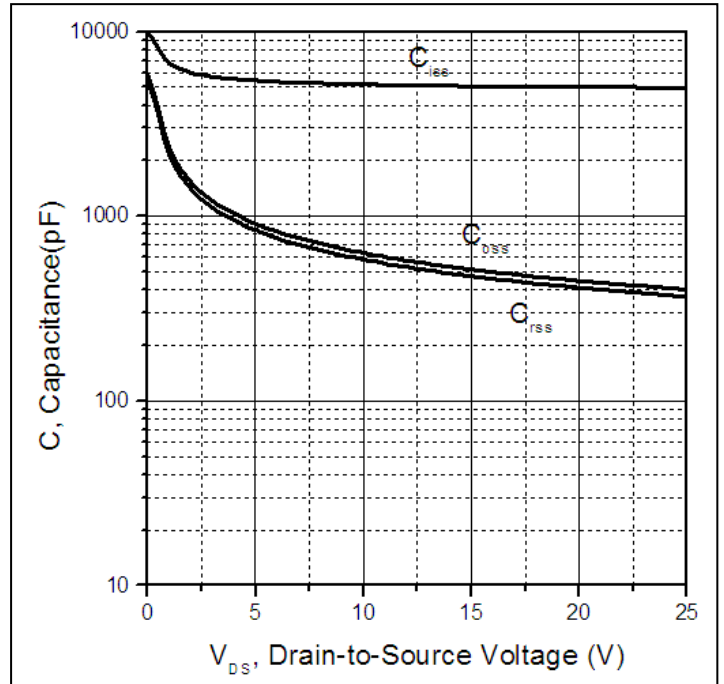


Figure 6. Typical Capacitance Vs. Drain-to-Source Voltage

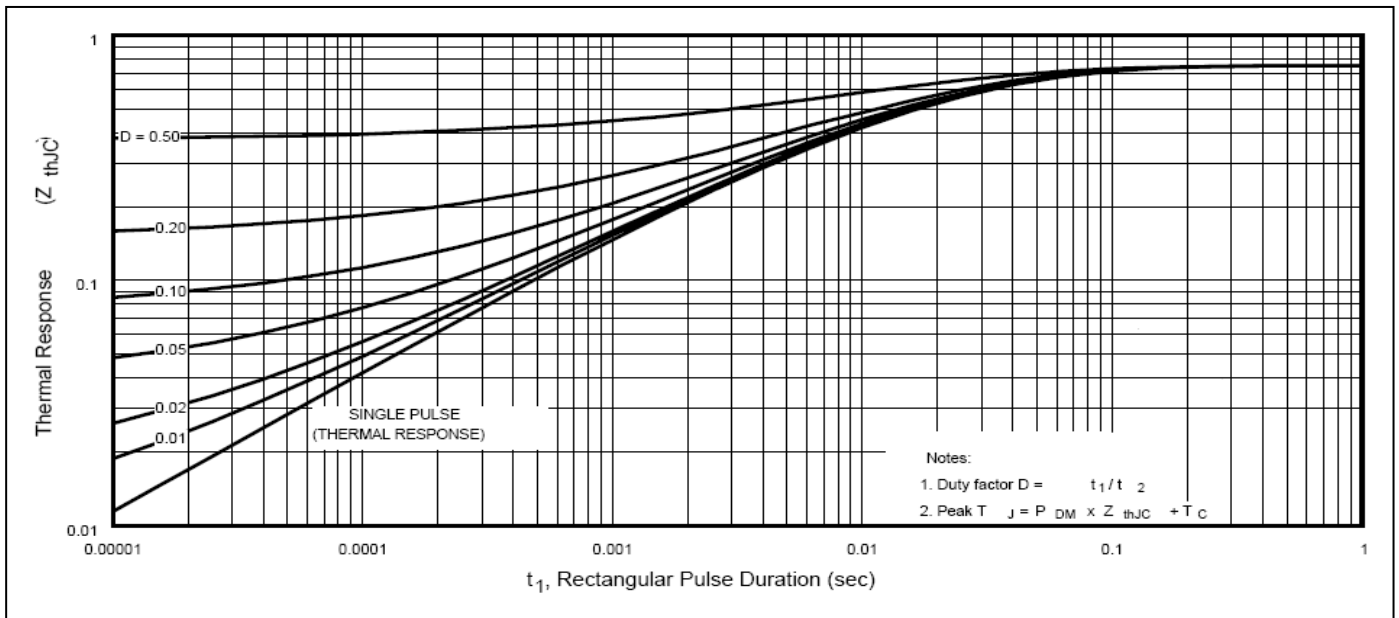
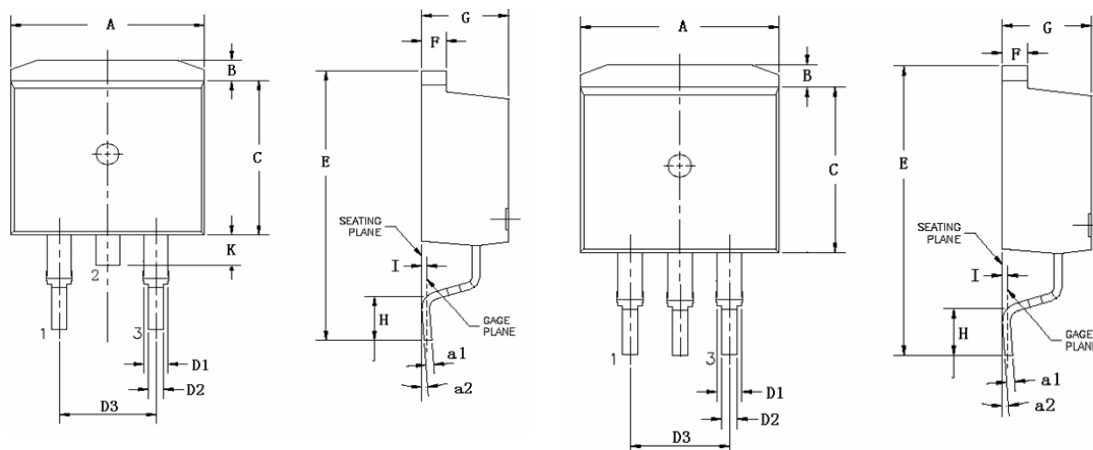


Figure 7. Maximum Effective Transient Thermal Impedance, Junction-to-Case

Mechanical Data:
TO263 PACKAGE OUTLINE DIMENSION


Symbol	Dimension In Millimeters		Dimension In Inches	
	Min	Max	Min	Max
A	9.660	10.280	0.380	0.405
B	1.020	1.320	0.040	0.052
C	8.590	9.400	0.338	0.370
D1	1.140	1.400	0.045	0.055
D2	0.700	0.950	0.028	0.037
D3	5.080 (TYP)		0.200 (TYP)	
E	15.090	15.390	0.594	0.606
F	1.150	1.400	0.045	0.055
G	4.300	4.700	0.169	0.185
H	2.290	2.790	0.090	0.110
I	0.250 (TYP)		0.010 (TYP)	
K	1.300	1.600	0.051	0.063
a1	0.450	0.650	0.018	0.026
a2	0 ⁰	8 ⁰	1 ⁰	8 ⁰

Ordering and Marking Information**Device Marking: SSF7508A****Package (Available)****D2PAK(TO263)****Operating Temperature Range****C : -55 to 175 °C****Devices per Unit**

Package Type	Units/Tube	Tubes/Inner Box	Units/Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
D2PAK	50	20	1000	6	6000

Reliability Test Program

Test Item	Conditions	Duration	Sample Size
High Temperature Reverse Bias(HTRB)	T_j=125°C to 175°C @ 80% of Max V_{DSS}/V_{CES}/V_R	168 hours 500 hours 1000 hours	3 lots x 77 devices
High Temperature Gate Bias(HTGB)	T_j=150°C or 175°C @ 100% of Max V_{GSS}	168 hours 500 hours 1000 hours	3 lots x 77 devices

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